

EL

Notice of Allowability	Application No.	Applicant(s)	
	10/033,715	BOWER, ROBERT W.	
	Examiner	Art Unit	
	Samuel A. Gebremariam	2811	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to 10/24/05.
2. ☒ The allowed claim(s) is/are 1,3-12,16-17 and 19-27.
3. ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) ☐ All b) ☐ Some* c) ☐ None of the:
 1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

* Certified copies not received: _____.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.

THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

4. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
5. ☐ CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 - (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) ☐ hereto or 2) ☐ to Paper No./Mail Date _____.
 - (b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.

Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).
6. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

- | | |
|---|--|
| 1. <input type="checkbox"/> Notice of References Cited (PTO-892) | 5. <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 2. <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 6. <input type="checkbox"/> Interview Summary (PTO-413),
Paper No./Mail Date _____. |
| 3. <input type="checkbox"/> Information Disclosure Statements (PTO-1449 or PTO/SB/08),
Paper No./Mail Date _____ | 7. <input checked="" type="checkbox"/> Examiner's Amendment/Comment |
| 4. <input type="checkbox"/> Examiner's Comment Regarding Requirement for Deposit
of Biological Material | 8. <input type="checkbox"/> Examiner's Statement of Reasons for Allowance |
| | 9. <input type="checkbox"/> Other _____. |

Steven Lake

DETAILED ACTION

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with John Obanion on 10/28/05.

2. The application has been amended as follows:

Claim 6, delete lines 1-7 and insert --- A multilayer light emitting device, comprising: a polysilicon layer; an oxide layer over said polysilicon layer; and a direct bandgap light emitting layer over said oxide layer, wherein electrons emitted from the polysilicon layer are converted into bandgap radiation by the light emitting layer; and wherein said polysilicon layer is formed with asperities that promote field emission of electrons into the oxide layer.---

Claim 8, delete lines 1-5 and insert--- A multilayer light emitting device, comprising: a polysilicon layer; an oxide layer over said polysilicon layer; and a GaInP layer over said oxide layer; wherein said polysilicon layer is formed with asperities that promote field emission of electrons into the oxide layer.---

Claim 9, line 2, delete "oxidized".

Claim 10, delete lines 1-5 and insert--- A multilayer light emitting device, comprising: a polysilicon layer; an oxide layer over said polysilicon layer; and a direct bandgap semiconductor layer over said oxide layer; wherein said polysilicon layer is formed with asperities that promote field emission of electrons into the oxide layer.---

Claim 22, delete lines 1-7 and insert---A method for generating light emission in a multilayer light emitting device, comprising: injecting electrons from a polysilicon layer through an oxide layer and into a direct bandgap light emitting layer where said electrons are converted into a bandgap radiation; wherein said polysilicon layer is formed with asperities that promote field emission of electrons into the oxide layer.---.

Claim 24, delete lines 1-7 and insert---A method for generating light emission in a multilayer light emitting device, comprising: injecting electrons from a polysilicon layer through an oxide layer and into a GaInP layer where said electrons are converted into bandgap radiation; wherein said polysilicon layer is formed with asperities that promote field emission of electrons into the oxide layer.---.

Claim 25, delete lines 1-8 and insert---A method for generating light emission in a multilayer light emitting device, comprising: injecting electrons from a polysilicon layer through an oxide layer and into a direct bandgap semiconductor layer where said

electrons are converted into bandgap radiation; wherein said polysilicon layer is formed with asperities that promote field emission of electrons into said oxide layer.---

Claim 27, delete lines 1-8 and insert--- A method for generating light emission in a multilayer light emitting device, comprising: injecting electrons from a polysilicon electron emitting layer through an oxide layer and into a GaInP layer where said electrons are converted into bandgap radiation; wherein said polysilicon layer is formed with asperities that promote field emission of electrons into said oxide layer.---

Allowance

3. Claims 1, 3-12, 16,17 and 19-27 are allowed.

Conclusion


4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Samuel A. Gebremariam whose telephone number is (571)-272-1653. The examiner can normally be reached on 8:00am-4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie Lee can be reached on (571) 272-1732. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Art Unit: 2811

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

SAG
October 31, 2005

A handwritten signature in cursive script, appearing to read "Steven Loke".